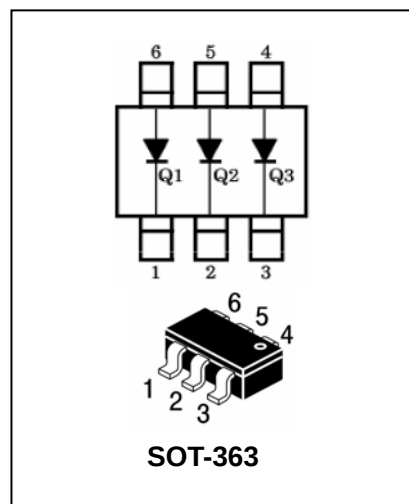


Surface Mount Schottky Barrier Diodes

SD103ATW

FEATURES

- Low forward voltage drop.
- Guard ring construction for transient protection.
- Fast switching.
- Low leakage current.
- Three fully isolated schottky diodes.
- Also available in lead free version.



APPLICATIONS

- High speed switching.

ORDERING INFORMATION

Type No.	Marking	Package Code
SD103ATW	KLL	SOT-363

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Characteristic	Value	Unit
V_{RRM} V_{RWM} V_R	Peak Repetitive reverse Voltage Working peak reverse voltage DC blocking voltage	40	V
$V_{R(RMS)}$	RMS reverse Voltage	28	V
I_{FM}	Forward continuous current (max.)	350	mA
I_O	Average rectified current	175	mA
I_{FSM}	Non-Repetitive peak forward surge current @t ≤10ms	1.0	A
$R_{\theta JA}$	Thermal resistance, Junction to ambient air	500	°C/W
P_D	Power Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +125	°C

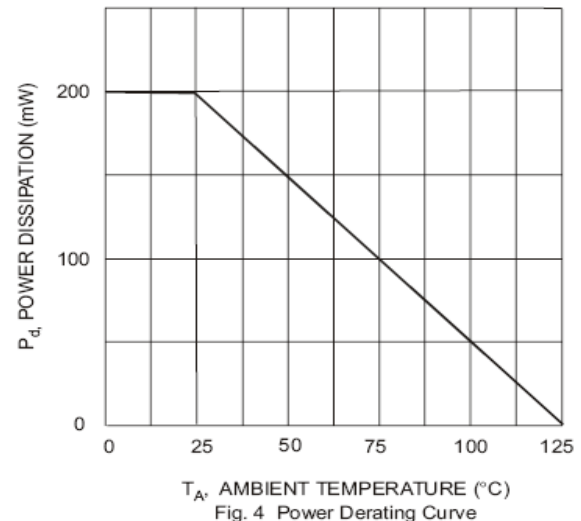
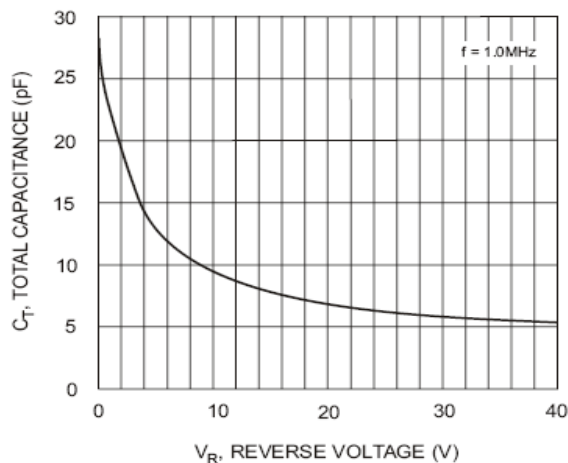
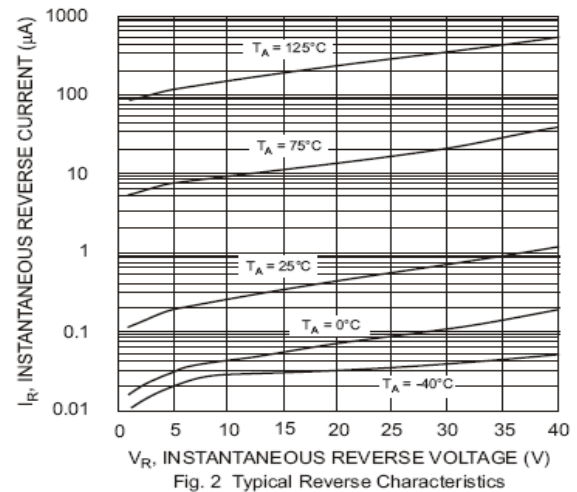
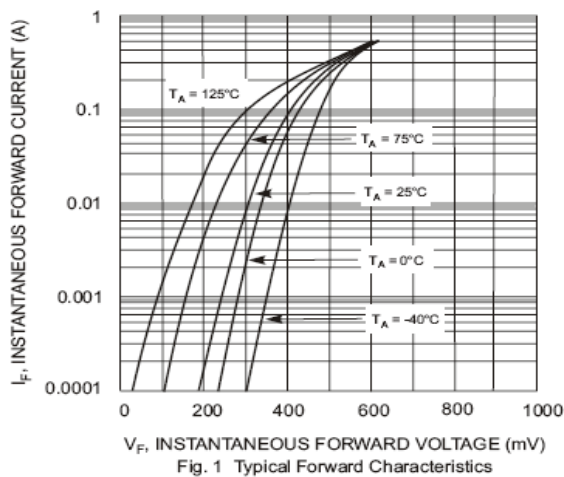
Surface Mount Schottky Barrier Diodes

SD103ATW

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu\text{A}$	40		-	V
Average reverse current	I_R	$V_R=10\text{V}$ $V_R=30\text{V}$		0.2 0.4	2.0 5.0	μA
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=5\text{mA}$ $I_F=20\text{mA}$ $I_F=100\text{mA}$	-	0.27 0.32 0.36 0.44	0.37 0.50	V
Total Capacitance	C_T	$V_R=0\text{V}, f=1.0\text{MHz}$	-	50	-	pF
Reverse recovery time	t_{rr}	$I_F=I_R=200\text{mA}, I_{rr}=0.1 \cdot I_R$ $R_L=100\Omega$	-	10	-	ns

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



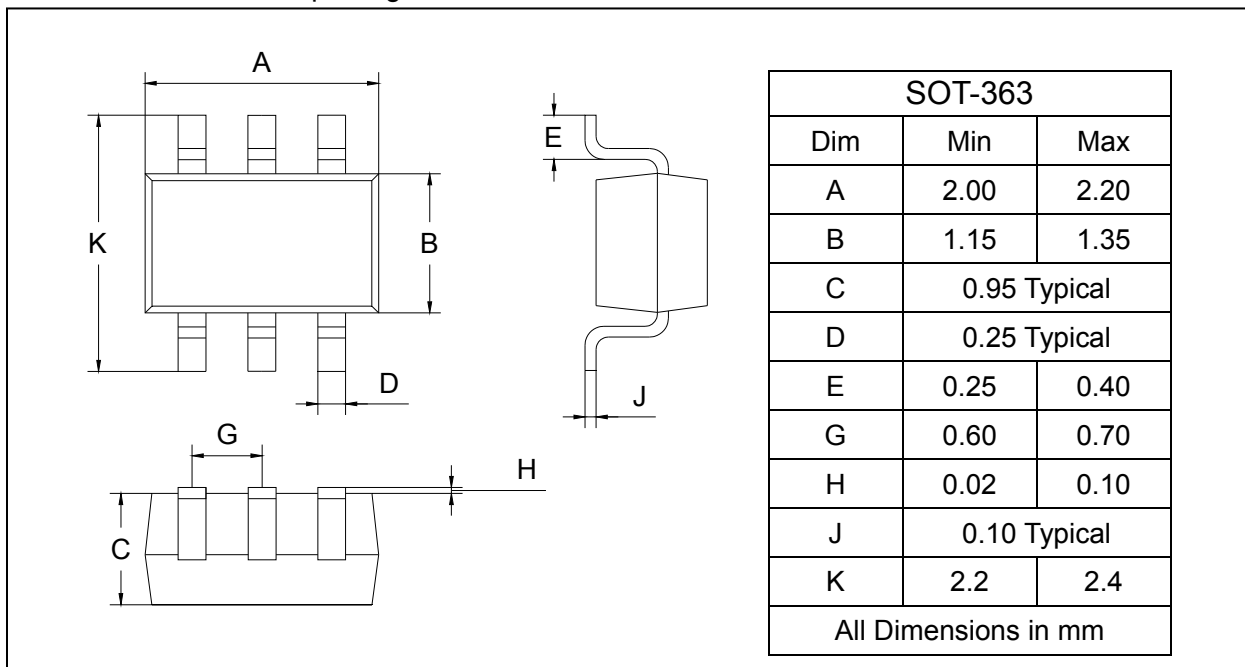
Surface Mount Schottky Barrier Diodes

SD103ATW

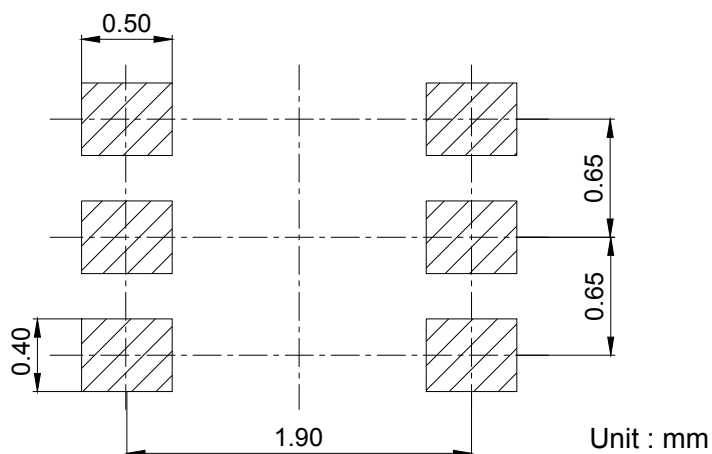
PACKAGE OUTLINE

Plastic surface mounted package

SOT-363



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
SD103ATW	SOT-363	3000/Tape&Reel